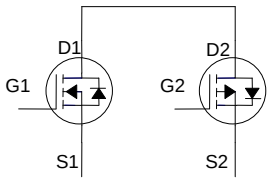
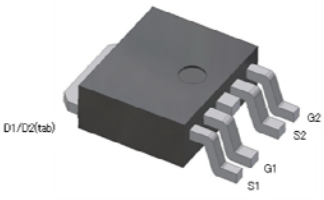
N & P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

	N-CH	P-CH
BV_{DSS}	40V	-40V
$R_{DSON\ (MAX.)}$	35mΩ	44mΩ
I_D	12A	-9A





Pb-Free Lead Plating & Halogen Free

GP
GREEN PRODUCT

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS		UNIT
Gate-Source Voltage		V_{GS}	N-CH	P-CH	V
			±20	±20	
Continuous Drain Current	T_C = 25 °C	I_D	12	-9	A
	T_C = 100 °C		8	-6	
Pulsed Drain Current[1]		I_{DM}	48	-36	
Power Dissipation	T_C = 25 °C	P_D	21		W
	T_C = 100 °C		8.3		
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		6	°C / W
Junction-to-Ambient	$R_{\theta JA}$		42	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	N-CH	40			V
		V_{GS} = 0V, I_D = -250μA	P-CH	-40			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	N-CH	1.8	2.3	3.2	
		V_{DS} = V_{GS}, I_D = -250μA	P-CH	-1.8	-2.3	-3.2	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	N-CH			±100	nA
		V_{DS} = 0V, V_{GS} = ±20V	P-CH			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 32V, V_{GS} = 0V	N-CH			1	μA
		V_{DS} = -32V, V_{GS} = 0V	P-CH			-1	
		V_{DS} = 30V, V_{GS} = 0V, T_J = 125 °C	N-CH			25	
		V_{DS} = -30V, V_{GS} = 0V, T_J = 125 °C	P-CH			-25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	N-CH	12			A
		V_{DS} = -5V, V_{GS} = -10V	P-CH	-9			
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 10A	N-CH		30	35	mΩ
		V_{GS} = -10V, I_D = -8A	P-CH		38	44	
		V_{GS} = 7V, I_D = 8A	N-CH		40	50	
		V_{GS} = -7V, I_D = -6A	P-CH		50	70	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 10A	N-CH		19		S
		V_{DS} = -5V, I_D = -8A	P-CH		11		
DYNAMIC							
Input Capacitance	C_{iss}	N-CH V_{GS} = 0V, V_{DS} = 20V, f = 1MHz P-CH V_{GS} = 0V, V_{DS} = -20V, f = 1MHz	N-CH		515		pF
			P-CH		745		
Output Capacitance	C_{oss}		N-CH		77		
			P-CH		78		
Reverse Transfer Capacitance	C_{rss}		N-CH		53		
			P-CH		58		

Total Gate Charge[1,2]	Q_g	N-CH V_{DS} = 20V, V_{GS} = 10V, I_D = 15A P-CH V_{DS} = -20V, V_{GS} = -10V, I_D = -10A	N-CH		13.1		nC
			P-CH		11.5		
Gate-Source Charge[1,2]	Q_{gs}		N-CH		1.9		
			P-CH		2.5		
Gate-Drain Charge[1,2]	Q_{gd}		N-CH		4.1		
			P-CH		2.8		
Turn-On Delay Time[1,2]	$t_{d(on)}$	N-CH V_{DS} = 10V, I_D = 1A, V_{GS} = 10V, R_{GS} = 6Ω P-CH V_{DS} = -10V, I_D = -1A, V_{GS} = -10V, R_{GS} = 6Ω	N-CH		2.5		nS
			P-CH		7		
Rise Time[1,2]	t_r		N-CH		7.5		
			P-CH		10		
Turn-Off Delay Time[1,2]	$t_{d(off)}$		N-CH		12		
			P-CH		20		
Fall Time[1,2]	t_f		N-CH		4		
			P-CH		12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)							
Continuous Current	I_S		N-CH			12	A
			P-CH			-9	
Pulsed Current[3]	I_{SM}		N-CH			48	
			P-CH			-36	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V	N-CH			1.3	V
			P-CH			-1.3	

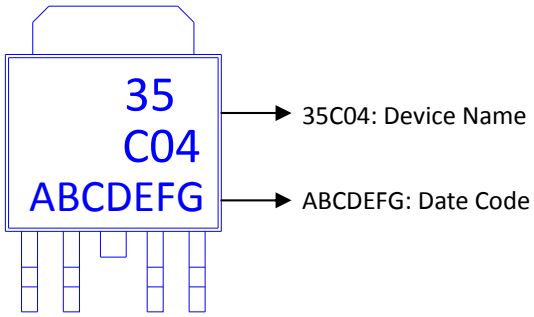
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

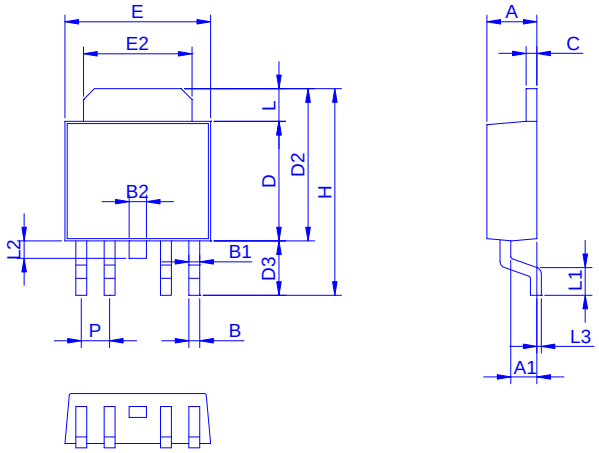
[3]Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: LB35C04D for DPAK (TO-252)

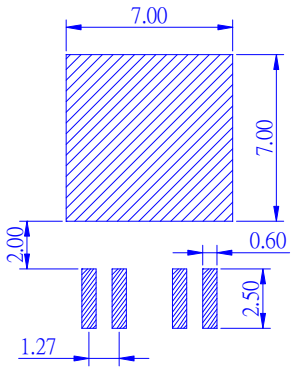


Outline Drawing

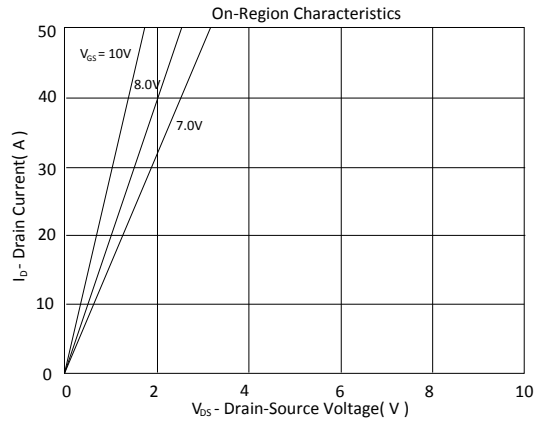


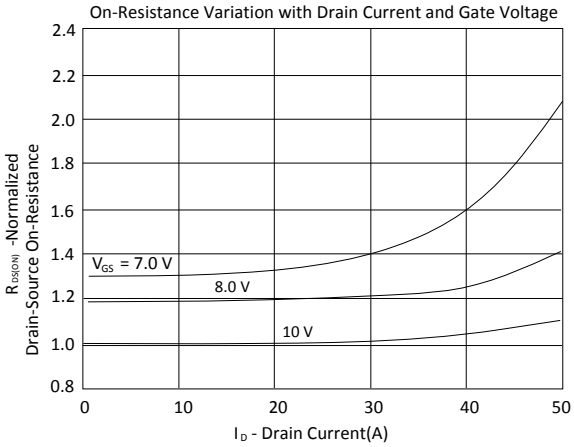
Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	1.10	0.30	0.55	0.40	0.40	5.30	6.70	2.20	6.30	4.80	9.20	1.30	0.90	0.50	0.00	1.17
Max.	2.50	1.30	0.70	0.75	0.80	0.60	5.70	7.30	3.00	6.70	5.45	10.15	1.70	1.50	1.10	0.30	1.37

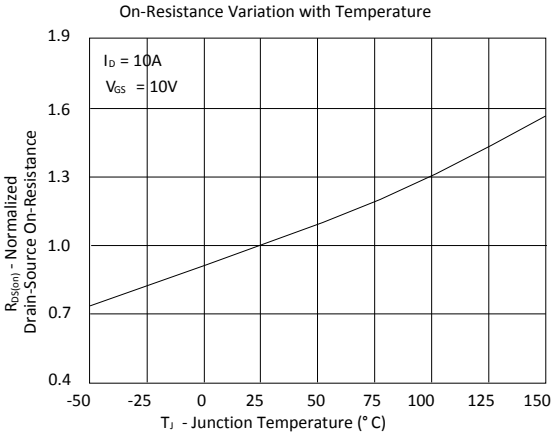
Footprint

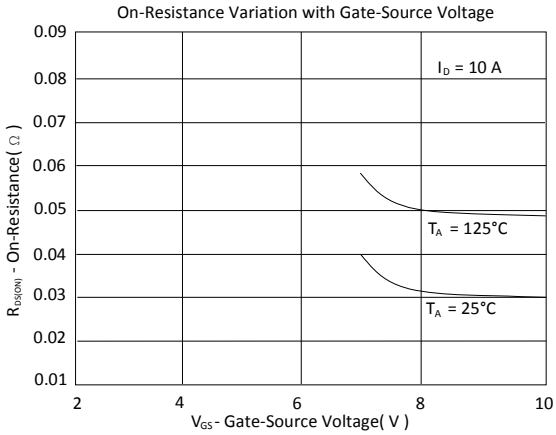


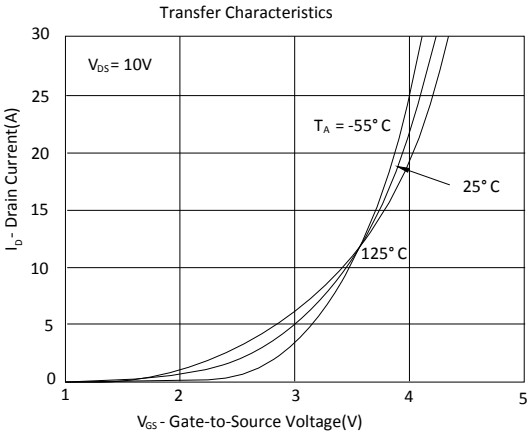
N-Channel

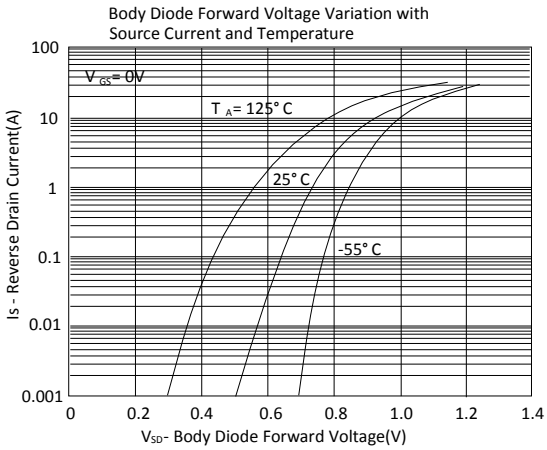

On-Region Characteristics
V_{GS} = 10V
8.0V
7.0V
I_D - Drain Current(A)
V_{DS} - Drain-Source Voltage(V)


On-Resistance Variation with Drain Current and Gate Voltage
V_{GS} = 7.0 V
8.0 V
10 V
$R_{DS(ON)}$ -Normalized
Drain-Source On-Resistance
I_D - Drain Current(A)

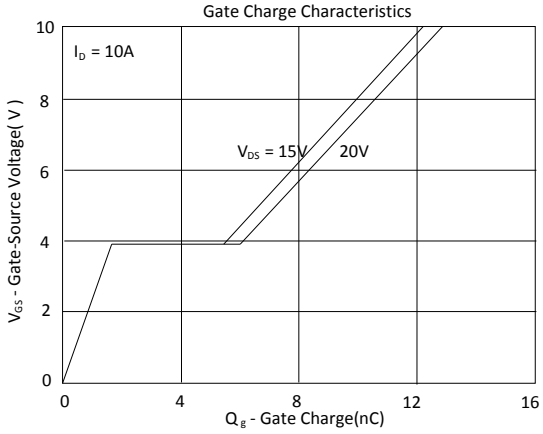

On-Resistance Variation with Temperature
I_D = 10A
V_{GS} = 10V
$R_{DS(on)}$ - Normalized
Drain-Source On-Resistance
T_J - Junction Temperature (° C)


On-Resistance Variation with Gate-Source Voltage
I_D = 10 A
T_A = 125°C
T_A = 25°C
$R_{DS(ON)}$ - On-Resistance(Ω)
V_{GS} - Gate-Source Voltage(V)

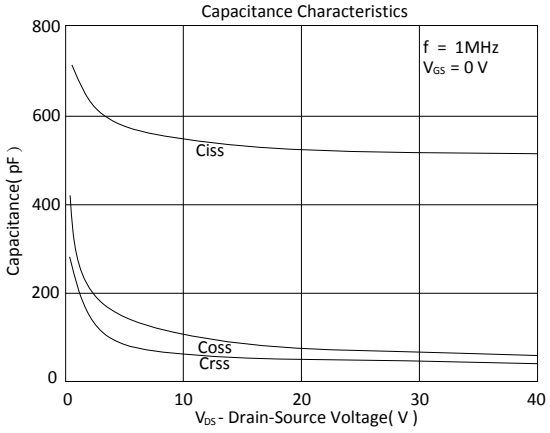

Transfer Characteristics
V_{DS} = 10V
T_A = -55° C
25° C
125° C
I_D - Drain Current(A)
V_{GS} - Gate-to-Source Voltage(V)


Body Diode Forward Voltage Variation with
Source Current and Temperature
V_{GS} = 0V
T_A = 125° C
25° C
-55° C
Is - Reverse Drain Current(A)
V_{SD} - Body Diode Forward Voltage(V)

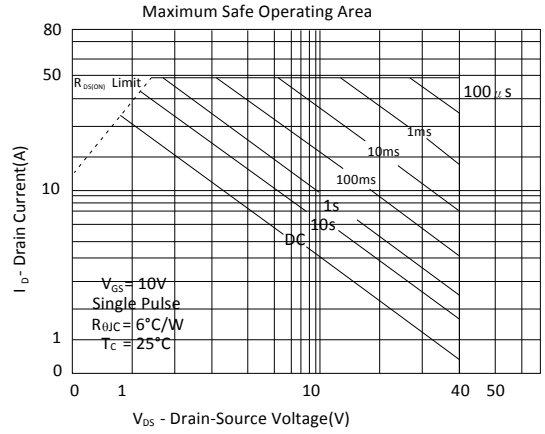
Gate Charge Characteristics



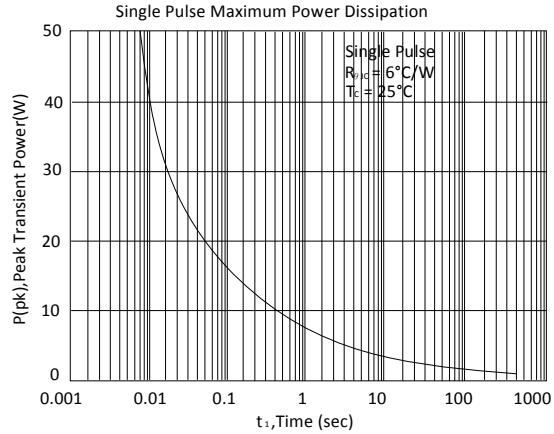
Capacitance Characteristics



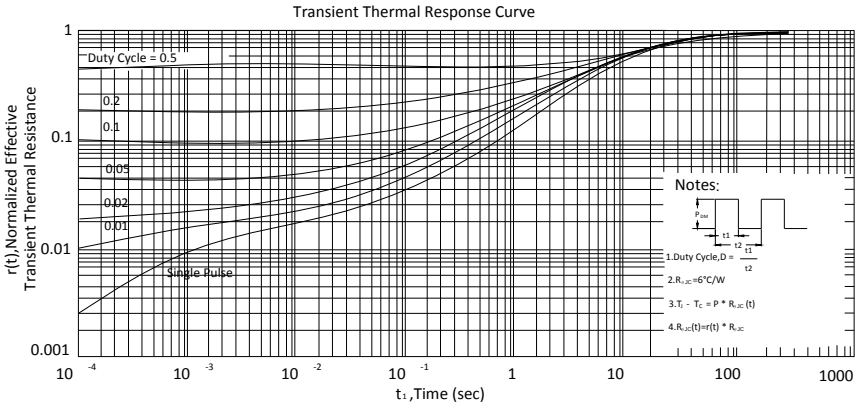
Maximum Safe Operating Area



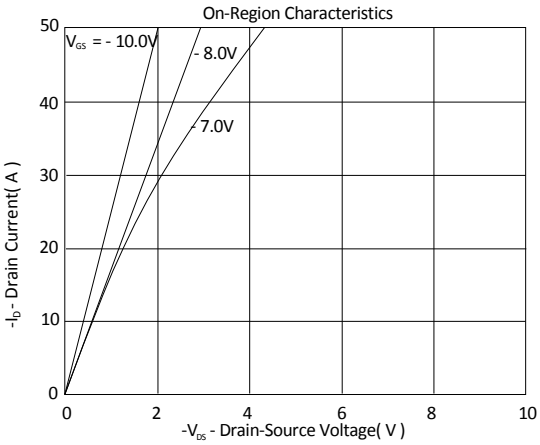
Single Pulse Maximum Power Dissipation

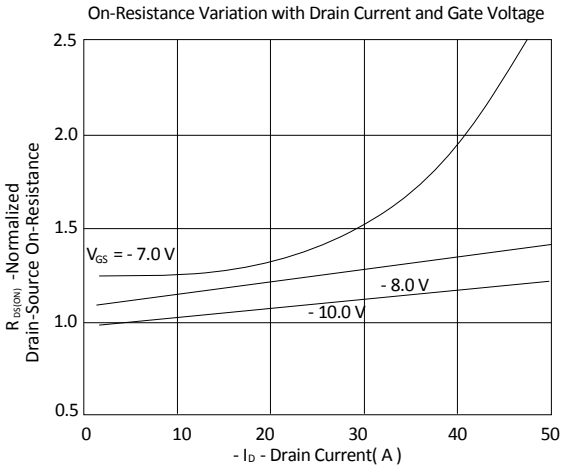


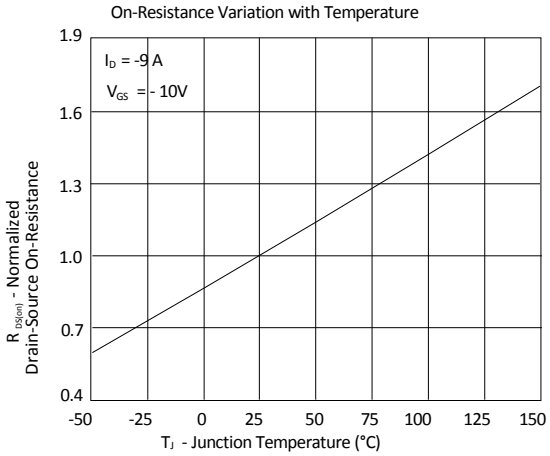
Transient Thermal Response Curve

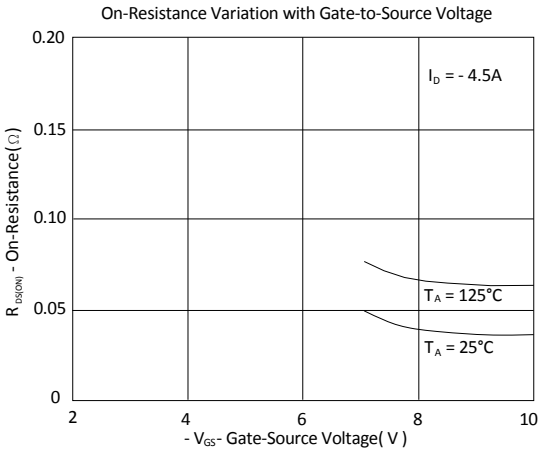


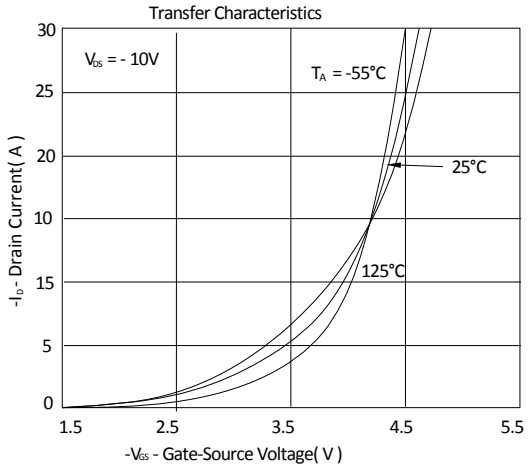
P-Channel

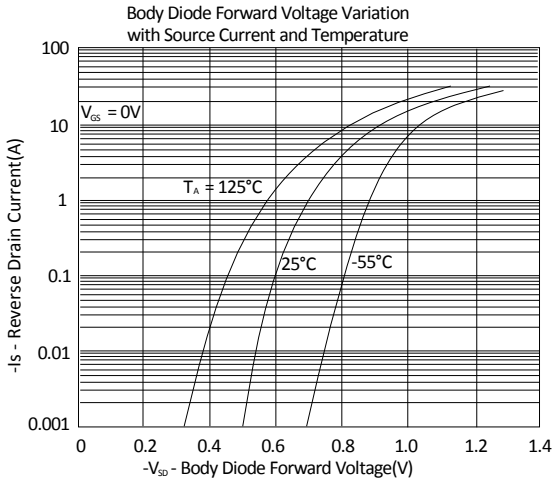

On-Region Characteristics
V_{GS} = - 10.0V
- 8.0V
- 7.0V
$-I_D$ - Drain Current(A)
$-V_{DS}$ - Drain-Source Voltage(V)


On-Resistance Variation with Drain Current and Gate Voltage
V_{GS} = - 7.0 V
- 8.0 V
- 10.0 V
$R_{DS(ON)}$ -Normalized
Drain-Source On-Resistance
- I_D - Drain Current(A)

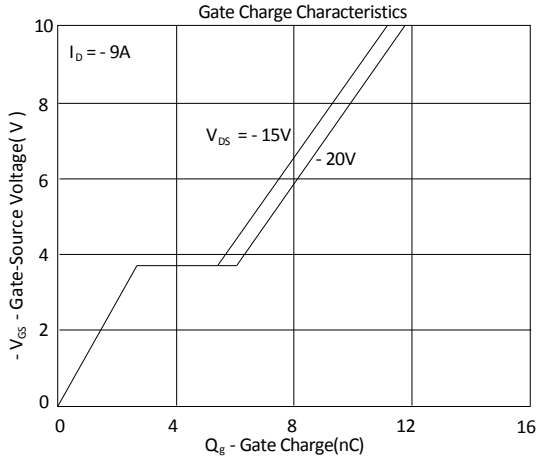

On-Resistance Variation with Temperature
I_D = -9 A
V_{GS} = - 10V
$R_{DS(on)}$ - Normalized
Drain-Source On-Resistance
T_J - Junction Temperature (°C)


On-Resistance Variation with Gate-to-Source Voltage
I_D = - 4.5A
T_A = 125°C
T_A = 25°C
$R_{DS(ON)}$ - On-Resistance(Ω)
- V_{GS}- Gate-Source Voltage(V)

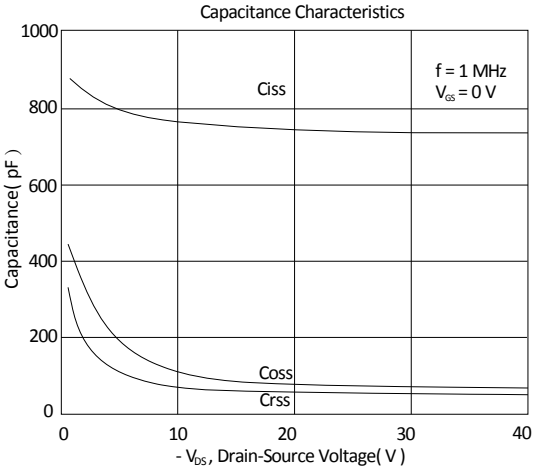

Transfer Characteristics
V_{DS} = - 10V
T_A = -55°C
25°C
125°C
$-I_D$ - Drain Current(A)
$-V_{GS}$ - Gate-Source Voltage(V)


Body Diode Forward Voltage Variation
with Source Current and Temperature
V_{GS} = 0V
T_A = 125°C
25°C
-55°C
-Is - Reverse Drain Current(A)
$-V_{SD}$ - Body Diode Forward Voltage(V)

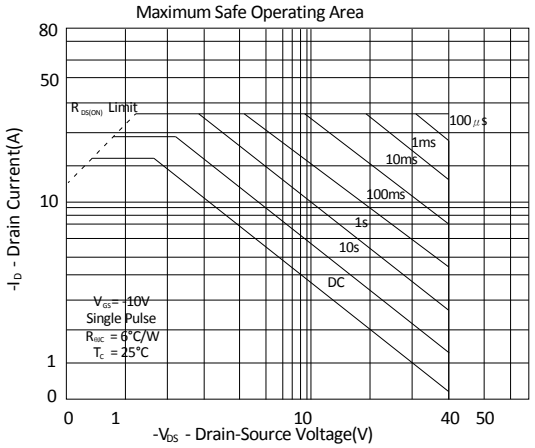
Gate Charge Characteristics



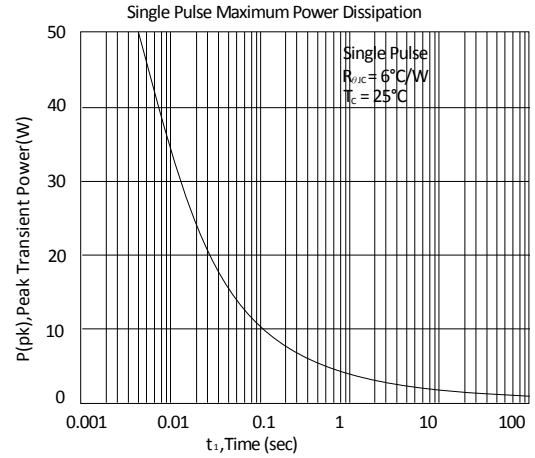
Capacitance Characteristics



Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Effective Transient Thermal Impedance